

Type	L#	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error ID
1	BRS	L1	628447 DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:54			0
2	BRS	L2	12833 vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:50			0
3	BRS	L3	3878 1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:55			0
4	BRS	L4	34706 (bury or buried) near3 (layer\$1 or film\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:56			0
5	BRS	L5	753 3 and 4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:40			0
6	BRS	L6	0 20040014329.URPN.	USPAT	2004/03/15 12:00			0

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Type	L#	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
7	BRS	L7	268974 source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:40			0
8	BRS	L8	16200 (remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or groov\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:42			0
9	BRS	L9	756023 (top or upper or second) near4 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:43			0
10	BRS	L10	121 5 and 7 and 8 and 9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:44			0
11	BRS	L11	47376 storage\$4 near4 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:45			0
12	BRS	L12	53 3 and 7 and 8 and 9 and 10 and 11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:49			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13	BRS	L13	758663 (lower or bottom or first) near4 (electrode\$1 or plate\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:42		0	
14	IS&R	L14	968 ((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or (438/248) or (438/249)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:45		0	
15	IS&R	L15	741 ((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:46		0	
16	BRS	L16	1293 14 or 15	USPAT; US-PGPUB	2004/03/15 15:47		0	
17	IS&R	L17	1892 ((438/136) or (438/137) or (438/138) or (438/206) or (438/241) or (438/242) or (438/268) or (438/270) or (438/271)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:50		0	
18	BRS	L18	46651 vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:50		0	

Type	L#	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
19	BRS	L19	124 18 and 1 and 4 and 7 and 8 and 9 and (11 or 13)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:08		0
20	BRS	L20	131 17 and 1 and 18 and 9 and (11 or 13)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:09		0
21	BRS	L21	129 16 and 1 and 18 and 9 and (11 or 13)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:09		0